

PLASTIC SILICON RECTIFIER

VOLTAGE RANGE: 200 --- 400 V
CURRENT: 3.0 A

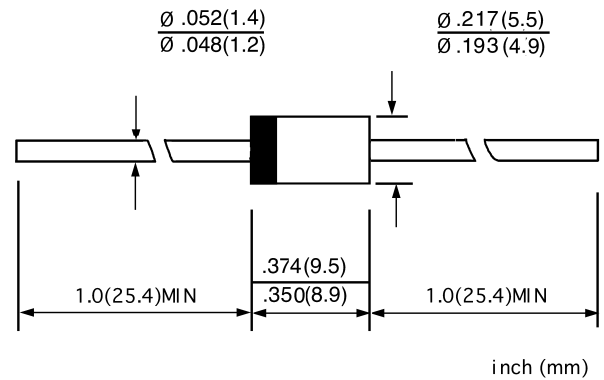
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon, Alcohol, Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO-27, molded plastic
- ◇ Terminals: Axial lead, solderable per MIL-STD-202, Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.041 ounces, 1.15 grams
- ◇ Mounting position: Any

DO - 27



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		ERD03 -02	ERD03 -04	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	200	400	V
Maximum RMS voltage	V_{RMS}	140	280	V
Maximum DC blocking voltage	V_{DC}	200	400	V
Maximum average forward rectified current 9.5mm lead length, @ $T_A=75^\circ C$	$I_{F(AV)}$	3.0		A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @ $T_J=125^\circ C$	I_{FSM}	200.0		A
Maximum instantaneous forward voltage @ 3.0 A	V_F	1.0		V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	10.0 100.0		μA
Typical junction capacitance (Note1)	C_J	35		pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	20		$^\circ C/W$
Operating junction temperature range	T_J	-55-----+150		$^\circ C$
Storage temperature range	T_{STG}	-55-----+150		$^\circ C$

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

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2. Thermal resistance from junction to ambient.

FIG.1 – TYPICAL FORWARD CHARACTERISTIC

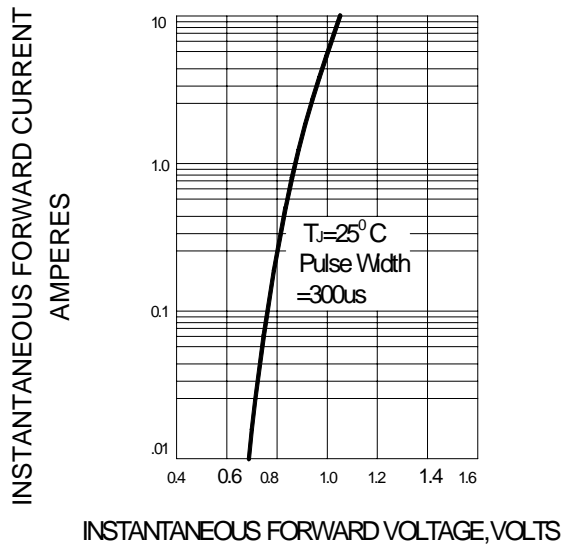


FIG.2 – TYPICAL JUNCTION CHARACTERISTICS

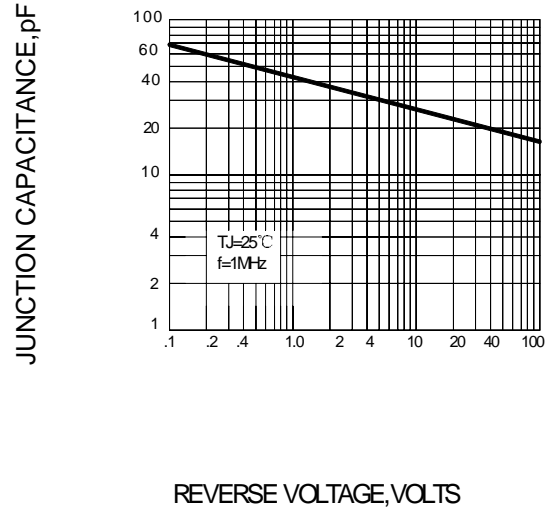


FIG.3 – FORWARD DERATING CURVE

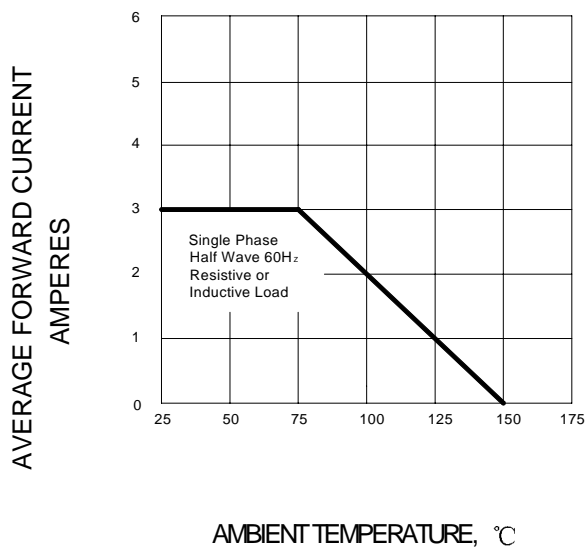


FIG.4 – PEAK FORWARD SURGE CURRENT

